



BUK7Y35-55B,115 Information

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For Reference Only

Part Number BUK7Y35-55B,115

Manufacturer NXP

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 55V 28.43A LFPAK

Package SC-100, SOT-669

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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BUK7Y35-55B,115 Specifications

Manufacturer Part Number BUK7Y35-55B,115 Manufacturer NXP Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SC-100, SOT-669 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 28.43A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 13.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 781pF @ 25V Vgs (Max) = 29V FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 35 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SC-100, SOT-669 Series SC-100, SOT-669 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) SUrrent - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 13.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 20V ### 20V ### 20V ### 20V ### 20V ### 20V ### 35 mOhm @ 15A, 10V Operating Temperature ### 35 mOhm @ 15A, 10V Departing Temperature ### 35 mOhm @ 15A, 10V Depart	Manufacturer Part Number	BUK7Y35-55B,115
Package SC-100, SOT-669 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 28.43A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 13.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 781pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 35 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Manufacturer	NXP
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Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 28.43A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 13.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 781pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 35 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 28.43A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 13.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 781pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 35 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	Package	SC-100, SOT-669
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 28.43A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 55V 28.43A (Tc) 10V 4V @ 1mA 4V @ 1mA 513.1nC @ 10V 781pF @ 25V ±20V FET F@ 25V ±20V FET Feature Supplier Device Package LFPAK56, Power-SO8 SC-100, SOT-669	Series	TrenchMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 28.43A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 13.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 781pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 35 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 10V 13.1nC @ 10V 781pF @ 25V ±20V FET (Power Dissipation (Max) 60W (Tc) 35 mOhm @ 15A, 10V -55°C ~ 175°C (TJ) Surface Mount LFPAK56, Power-SO8 SC-100, SOT-669	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 781pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 35 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	Current - Continuous Drain (Id) @ 25°C	28.43A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 781pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 35 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surface Mount Supplier Device Package Package / Case T81pF @ 25V 781pF @ 25V 8 Surface Mount LFPAK56, Power-SO8 SC-100, SOT-669	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)60W (Tc)Rds On (Max) @ Id, Vgs35 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageLFPAK56, Power-SO8Package / CaseSC-100, SOT-669	Gate Charge (Qg) (Max) @ Vgs	13.1nC @ 10V
FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 35 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Input Capacitance (Ciss) (Max) @ Vds	781pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs35 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageLFPAK56, Power-SO8Package / CaseSC-100, SOT-669	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Power Dissipation (Max)	60W (Tc)
Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Rds On (Max) @ Id, Vgs	35 mOhm @ 15A, 10V
Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case SC-100, SOT-669	Mounting Type	Surface Mount
	Supplier Device Package	LFPAK56, Power-SO8
Report errors?	Package / Case	SC-100, SOT-669
		Report errors?

BUK7Y35-55B,115 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

BUK7Y35-55B,115 Payment Methods



















BUK7Y35-55B,115 Shipping Methods













If you have any question about BUK7Y35-55B,115, please do not hesitate to contact us!

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